AOS Semiconductor
Product Reliability Report

AO4286, rev B

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

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This AOS product reliability report summarizes the qualification result for AO4286. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4286 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

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I. Product Description:

The AO4286 uses trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$, Ciss and Coss.
This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Details refer to the datasheet.

II. Die / Package Information:

	AO4286
Process	Standard sub-micron 100V N-Channel MOSFET
Package Type	SO8
Lead Frame	Bare Cu
Die Attach	Ag Epoxy
Bond	Cu wire
Mold Material	Epoxy resin with silica filler
Moisture Level	Up to Level 1

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III. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
MSL Precondition	168hr 85°C / 85%RH + 3 cycle reflow@260°C (MSL 1)	-	4158 pcs	0	JESD22-A113
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
HTRB	Temp = 150°C , Vds=80% of Vdsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
HAST	130°C , 85%RH, 33.3 psi, Vds = 80% of Vdsmax	96 hours	924 pcs	0	JESD22-A110
H3TRB	85°C , 85%RH, Vds = 80% of Vdsmax	1000 hrs	693 pcs	0	JESD22-A101
Autoclave	121°C , 29.7psi, RH=100%	96 hours	924 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air,	250 / 500 cycles	924 pcs	0	JESD22-A104
HTSL	Temp = 150°C	1000 hrs	693 pcs	0	JESD22-A103

Note: The reliability data presents total of available generic data up to the published date.

IV. Reliability Evaluation

FIT rate (per billion): 3.27
MTTF = 34926 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $Chi^2 \times 10^9$ **/ [**2 (N) (H) (Af)**] =** 3.27
MTTF = 10^9 / FIT = 34926 years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval
N = Total Number of units from burn-in tests
H = Duration of burn-in testing
Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)
Acceleration Factor [**Af**] = **Exp** [Ea / **k** (1/Tj u – 1/Tj s)]
Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	**259**	**87**	**32**	**13**	**5.64**	**2.59**	**1**

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16
Tj u =The use junction temperature in degree (Kelvin), K = C+273.16
k = Boltzmann's constant, 8.617164 X 10^{-5}eV / K